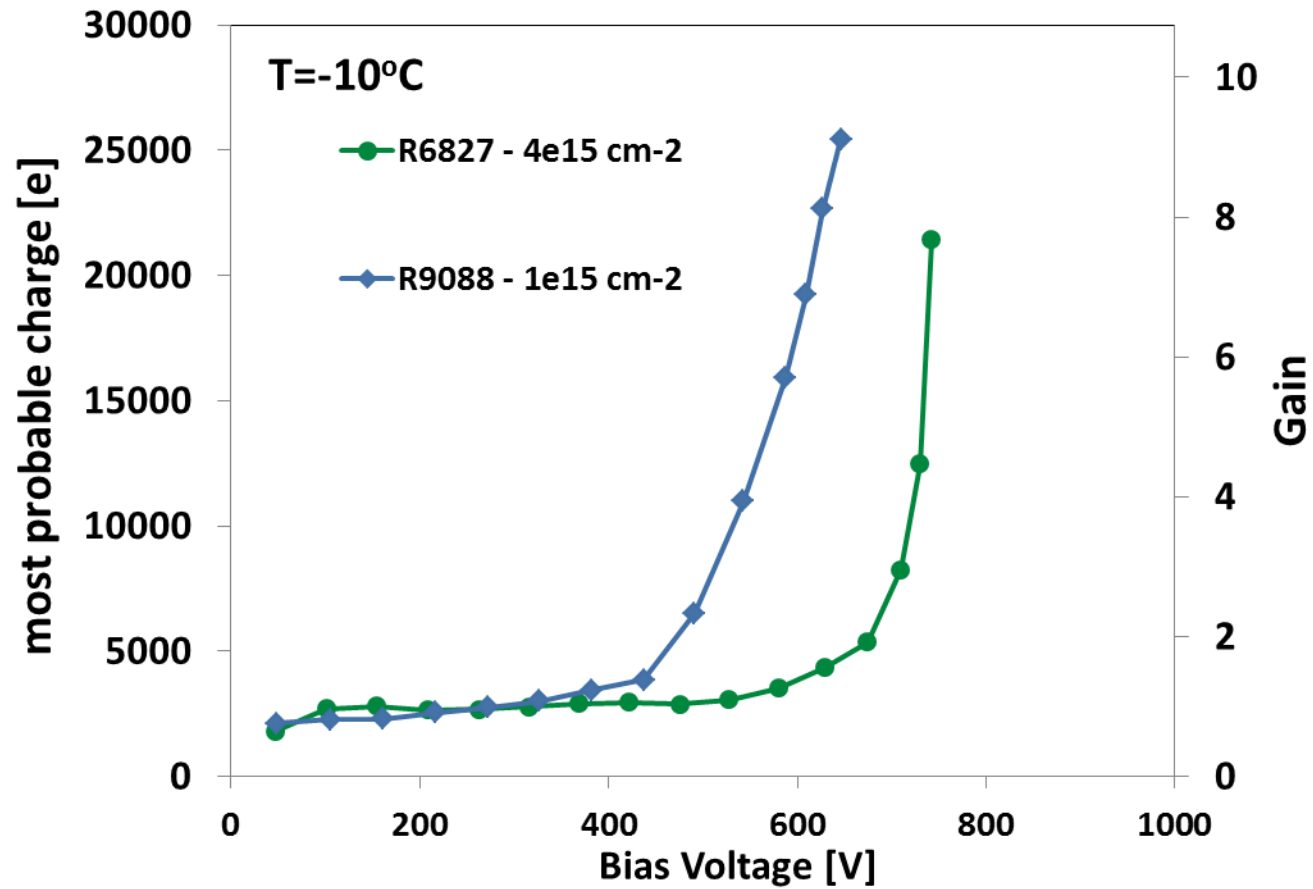


Dependence of most probable charge on voltage for minimum ionizing electrons ( $^{90}\text{Sr}$ ) in 50  $\mu\text{m}$  thick LGAD detectors after neutron irradiation to different equivalent fluences. The sensors are from two different runs, R6827 on epitaxial and R9088 on SOI wafers. The gain is given as a ratio between the collected charge in the LGAD and in the non-irradiated control sample (pin diode).



Dependence of most probable charge on voltage for minimum ionizing electrons (<sup>90</sup>Sr) in 50 μm thick LGAD detectors after neutron irradiation to different equivalent fluences. The sensors are from two different runs, R6827 on epitaxial and R9088 on SOI wafers. The gain is given as a ratio between the collected charge in the LGAD and in the non-irradiated control sample (pin diode).